

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
FUSO1.001AUSAPPLICATION NO.
09/918,018INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Hitoshi Shimizu *et al*FILING DATE
July 30, 2001GROUP
2881

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
<i>AR</i>	WO 00/38287	29.06.00	PCT				
<i>AR</i>	WO 01/33677 A2	10.05.01	WIPO				

EXAMINER
INITIAL

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

<i>AR</i>	H. Shimizu et al., 1.2 um range GaInAs S QW lasers using Sb as surfactant, <u>ELECTRONICS LETTERS</u> , Vol. 36, No. 16, August 3, 2000, 2 pages.
<i>AR</i>	X. Yang et al., Molecular beam epitaxial growth of InGaAsN:Sb/GaAs quantum wells for long-wavelength semiconductor lasers, <u>Applied Physics Letters</u> , Vol. 75, No. 2, July 12, 1999, pp. 178-180.
<i>AR</i>	X. Yang et al., Photoluminescence of as-grown and thermally annealed InGaAsN/GaAs quantum wells grown by molecular beam epitaxy, <u>J. Vac. Sci. Technol.</u> , Vol. B, No. 17(3), May/June 1999, pp. 1144-1146.
<i>AR</i>	X. Yang et al., Low-Threshold 1.3-um InGaAsN:Sb-GaAs Single-Quantum-Well Lasers Grown by Molecular Beam Epitaxy, <u>IEEE PHOTONICS TECHNOLOGY LETTERS</u> , Vol. 12, No. 2, February 2000, pp. 128-130.

H:\DOCS\MJG\MJG-4777.DOC 063003

EXAMINER

Hermando Rodriguez

DATE CONSIDERED

5-25-04

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 608; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.